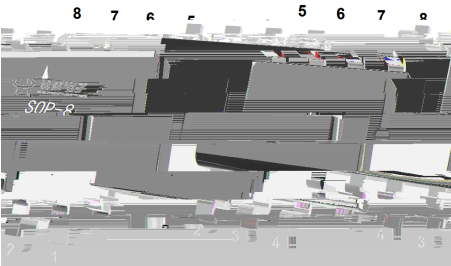


9 5 6 .> // x 6 ?ú 3 3 5 9 « | • 'ož
P-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

$V_{DS} (V) = -30V$ $I_D = -16A$ ($V_{GS} = \pm 20V$)
 $R_{DS(ON)}@-10V$ "8.0m (Typ.7.0m)
 $R_{DS(ON)}@-4.5V$ "15m (Typ.10.3m)
—)í D }ož HF Product.

9 > ' ò k Ž ` " — Œ y P ^ © İož
Power Management in Notebook computer, Portable Equipment and Battery powered systems.



PIN1 y S PIN 2 y S PIN 3 y S PIN 4 y G
PIN 5 y



@ f Parameter		... Z Symbol	f > Rating	% y Unit
Drain-Source Voltage		V _{DS}	-30	V
Drain Current - Continuous		I _D	-16	A
Drain Current – Pulsed		I _{DM}	-65	A
Gate-Source Voltage		V _{GS}	±20	V
Power Dissipation		P _D	3	W
Single Pulse Avalanche Energy(L=0.5mH)		E _{AS}	360	mJ
Avalanche Current(L=0.5mH)		I _{AS}	-30	A
Junction and Storage Temperature Range		T _j , T _{stg}	-55 to 150	-
Thermal resistance, junction - ambient	t 0 10s	R _{JA}	41.7	- / W
	Steady-State		75	

@ f Parameter	... Z Symbol	y i Ú ^ Test Conditions	Â 4 > Min	Á ° > Typ	Â Ý > Max	% y Unit
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =-250 A V _{GS} =0V	-30	-35		V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V V _{GS} =0V			-1	uA
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} = ±20V			f 100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =-250 A	-1	-1.5	-2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-10A		7.0	8	m S
		V _{GS} =-4.5V, I _D =-8A		10.3	15	
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V			-1.2	V
Input Capacitance	C _{iss}	V _{DS} =-25V V _{GS} =0V f=1.0MHz		3260		pF
Output Capacitance	C _{oss}			335		

Electrical Characteristics (Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	t _{d(on)}	V _{GS} =-10V V _{DS} =-15V R _L =0.75 Ω R _{GEN} =3 Ω		12.5		ns
Turn-On Rise Time	t _r			19		
Turn-Off Delay Time	t _{d(off)}			125		
Turn-Off Fall Time	t _f			67		

Electrical Characteristics

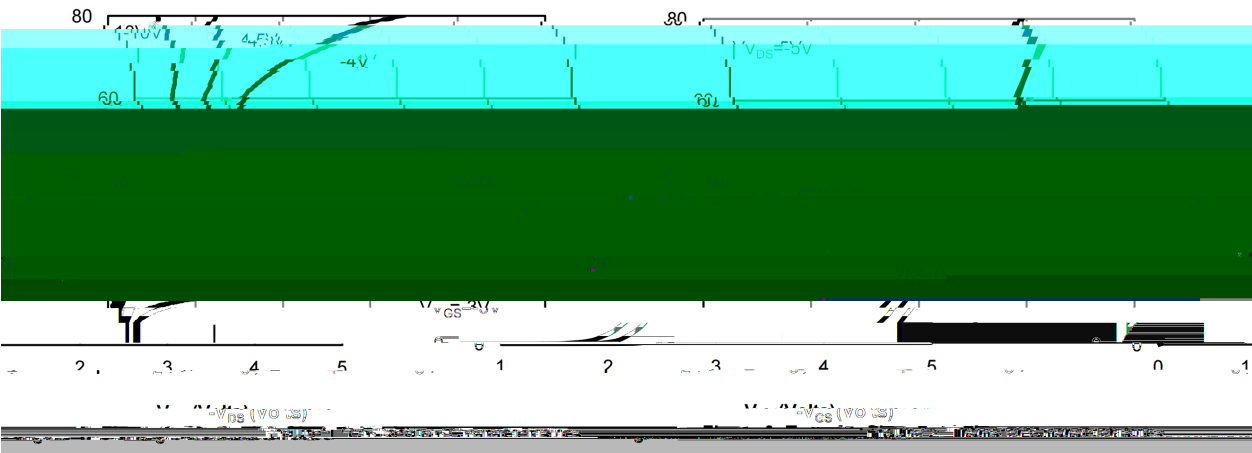
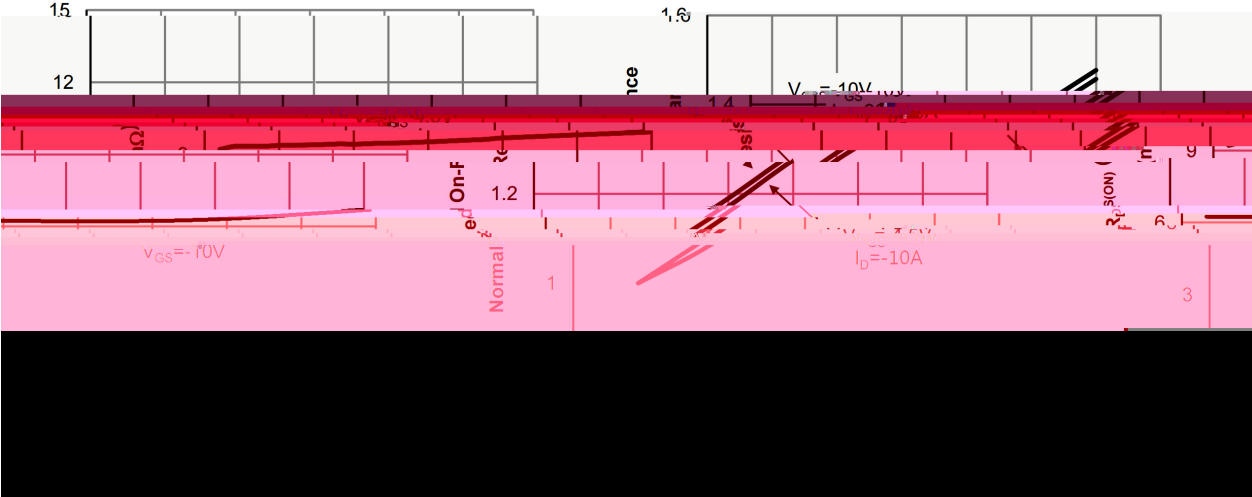
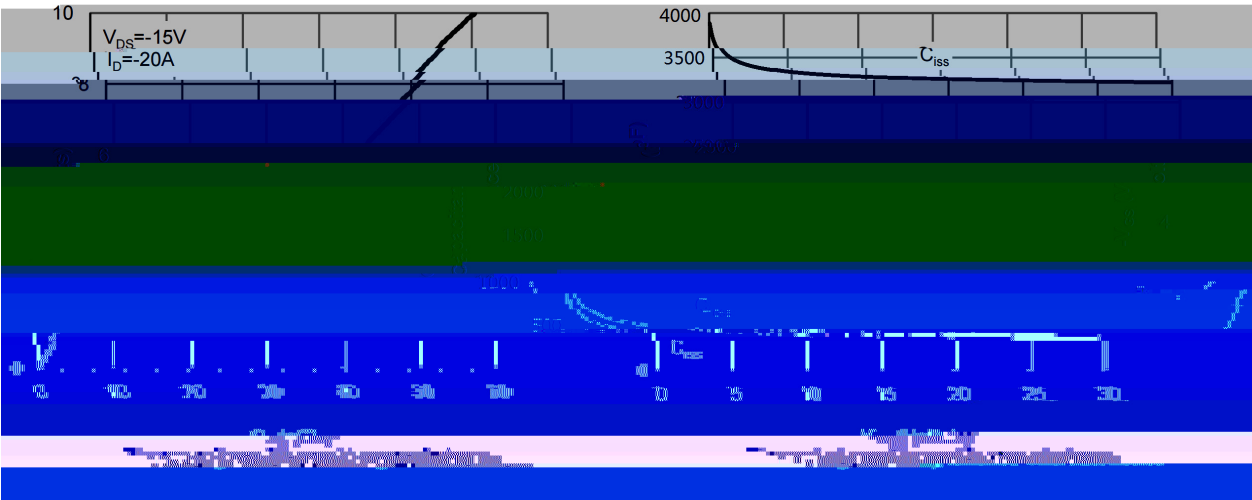
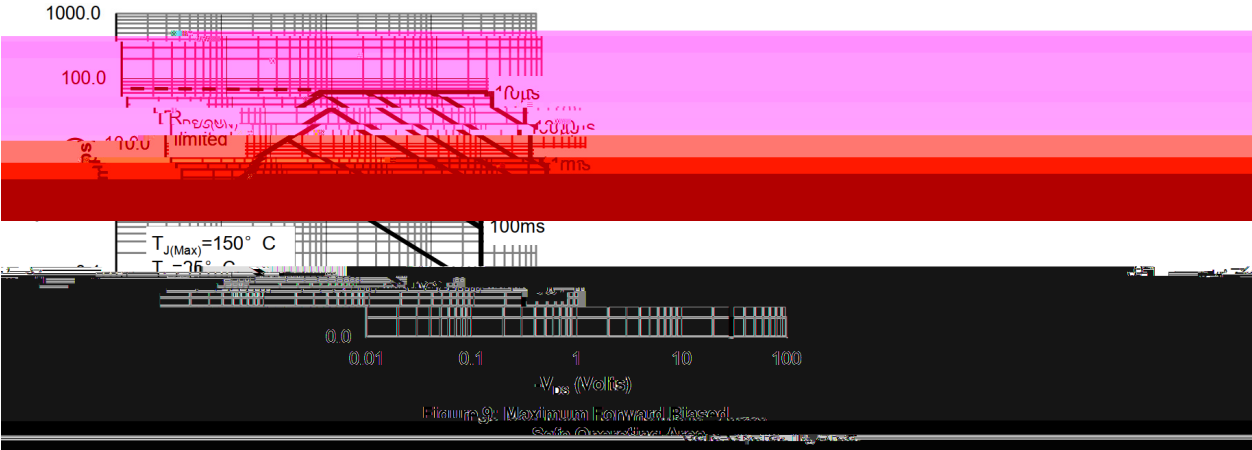
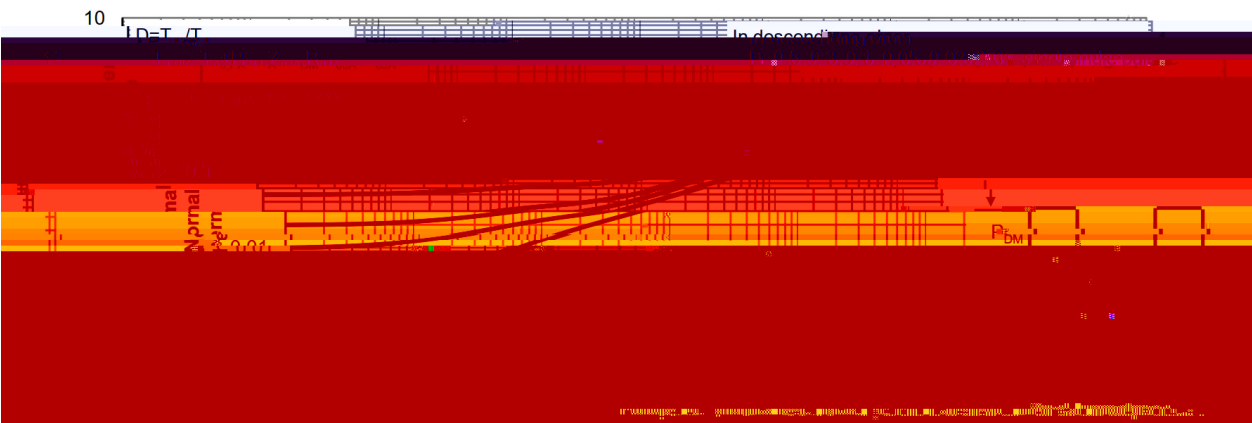
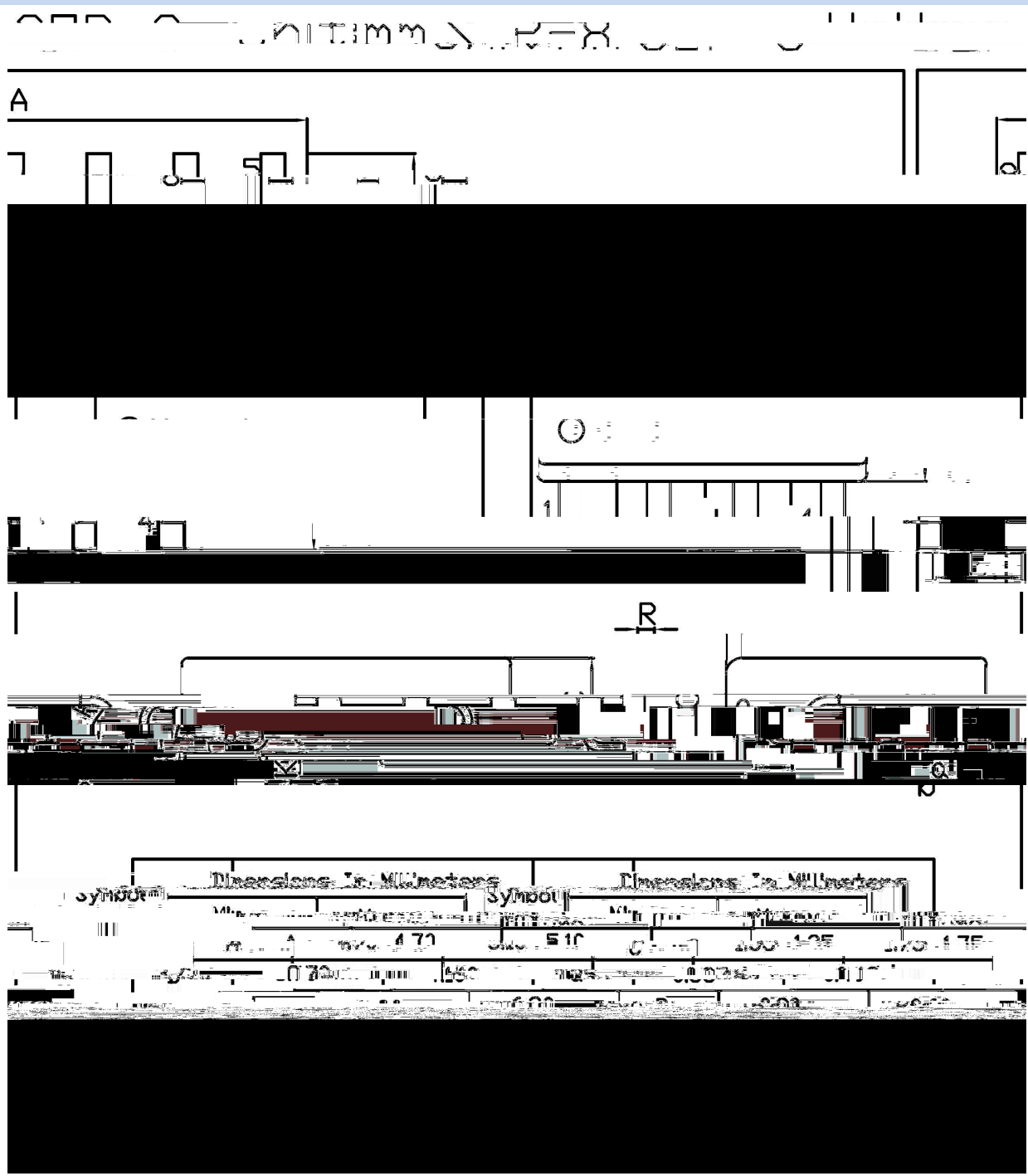


Figure 6: Body-Diode Characteristics Figure 7: Transfer Characteristics Figure 8: Forward Characteristics

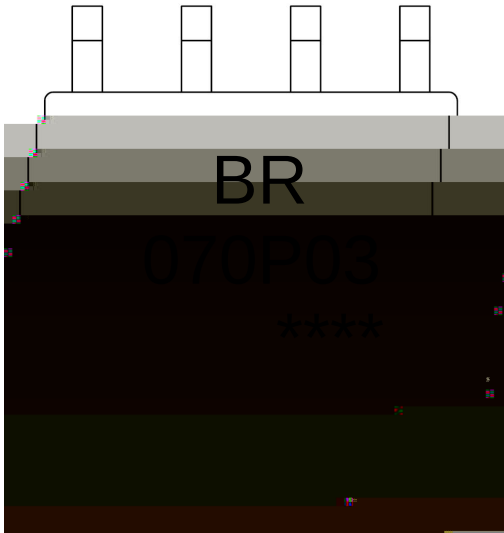
Electrical Characteristics



Ø □ =) ☐ / Package Dimensions



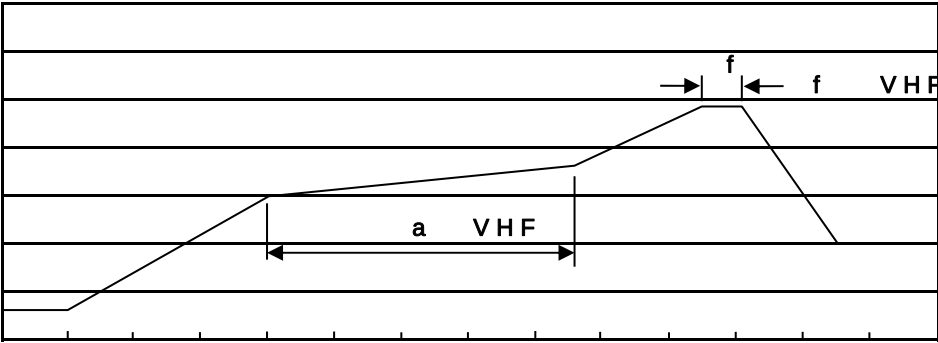
1. Main Features / Making Instructions



1. Main Features
- BR: Company Code
- 070P03: Product Type Code
- ****: Lot No. Code, code change with Lot No

šWD t...•Žč (x/) / :KSVKXGZ[XK 6XULORK LUX /8 8KLRU] 9URJKXOTM 6

7HPSHUDWXUH



7LPH VHF

ačy

- 10• Ä½ “† 150½180 - kž• 60½90sec;
- 20• Q> “† 245 r5 - kž• 4 Ò 5 r0.5sec;
- 30•D Nò i Ò 0 ,† 2½10 - /sec.

Note:

- 1.Preheating:150~180 - , Time:60~90sec.
- 2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.
- 3. Cooling Speed: 2~10 - /sec.

ÂD /Că p ¯ »] / Reinnce b Soldering HeatTetCconditons

“†y 260 r5 - ž•y 10 r1 sec. Temp.:260±5 Time:10±1 sec

G P á / Packaging SPEC.

2 & x / REEL

Package Type 7>û ~ E	Units ;>û H					Dimension ;>û p . (unit /Æmm³)		
	Units/Reel /-	Reels/Inner Box -- /-	Units/Inner Box /-	Inner Boxes/Outer Box - /1ç	Units/Outer Box /1ç	Reel	Inner Box	Outer Boxç
SOP/ESOP-8	4,000	2	8,000	6	48,000	13 s ×12	360×360×50	380×335×366

„Đ y f / Notces